Abstracts

DC and RF Techniques for Computing Access Resistances in Microwave FET's

J.A. Reynoso-Hernandez and F.E. Rangel-Patino. "DC and RF Techniques for Computing Access Resistances in Microwave FET's." 1996 MTT-S International Microwave Symposium Digest 96.3 (1996 Vol. III [MWSYM]): 1711-1714.

In order to estimate the access resistances of PHEMTs two different techniques based on I(V) and RF measurements were investigated. An improved cold-FET technique is presented. The main difference between the classical and the proposed cold-FET techniques lies on the open circuit condition in drain-source instead of short circuit condition (V/sub DS/=0 V). A good agreement is observed between the values of parasitic resistances computed from DC I(V) and RF measurements.

❑ Return to main document.